



Product data sheet

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

3. Applications

• Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

| Symbol | Parameter | Conditions | | | Values | | |
|------------------|------------------------------------|--|---------|-----|--------|-------|------|
| Absolute | maximum rating | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | | 2 | 00 | | V |
| $I_{F(AV)}$ | average forward current | δ = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2 | 8 | | | А | |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 128 °C; square-wave pulse | 16 | | | А | |
| I _{FSM} | non-repetitive peak | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 80 | | | А | |
| forward current | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 88 | | | А | |
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| Static ch | aracteristics | | , | | | | |
| V _F | forward voltage | I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u> | | - | 0.8 | 0.895 | V |
| Dynamic | characteristics | | | | | - | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery; Fig. 5; Fig. 7}$ | - 20 25 | | ns | | |
| Electros | atic discharge | | | | | · | |
| V_{ESD} | electrostatic discharge voltage | HBM; C = 250 pF; R = 1.5 kΩ | | - | - | 8 | kV |

5. Pinning information

| Table | 2. | Pinning | g information | 1 |
|-------|----|---------|---------------|----|
| Tuble | | | g innormation | ۰. |

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|------------------------|--------------------|----------------|
| 1 | К | cathode | mb | |
| 2 | А | anode | j O f | К — К — А |
| mb | mb | mounting base; cathode | C | 001aaa020 |

6. Ordering information

| Table 3. Ordering information | | | | | | |
|-------------------------------|----------|---|---------|--|--|--|
| Type number | Package | | | | | |
| | Name | Description | Version | | | |
| BYW29E-200 | TO-220AC | plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC | SOD59 | | | |

7. Marking

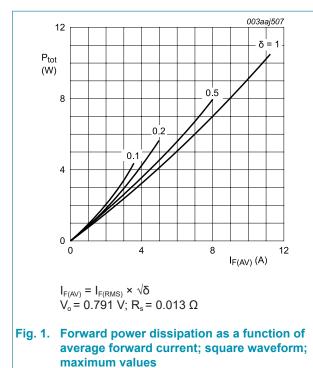
| Table 4. Marking codes | |
|------------------------|---------------|
| Type number | Marking codes |
| BYW29E-200 | BYW29E-200 |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
|------------------|--|--|------------|------|
| V _{RRM} | repetitive peak reverse voltage | | 200 | V |
| V_{RWM} | crest working reverse voltage | | 200 | V |
| V _R | reverse voltage | | 200 | V |
| $I_{F(AV)}$ | average forward current | δ = 0.5; T _{mb} ≤ 128 °C ;square-wave pulse; Fig. 1; Fig. 2 | 8 | A |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 128 °C; square-wave pulse | 16 | A |
| I _{FSM} | non-repetitive peak | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 80 | A |
| forwa | forward current | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 88 | A |
| I _{RRM} | repetitive peak reverse current | δ = 0.001; t _p = 2 μs | 0.2 | A |
| I _{RSM} | non-repetitive peak reverse current | t _p = 100 μs | 0.2 | A |
| T _{stg} | storage temperature | | -40 to 150 | °C |
| T _j | junction temperature | | 150 | °C |
| Electrosta | atic discharge | , | | |
| V_{ESD} | electrostatic discharge voltage | HBM; C = 250 pF; R = 1.5 kΩ | 8 | kV |



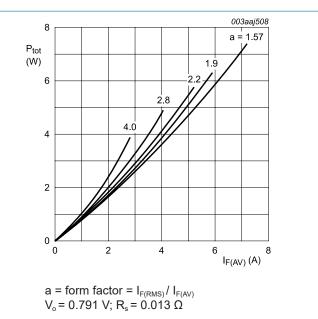
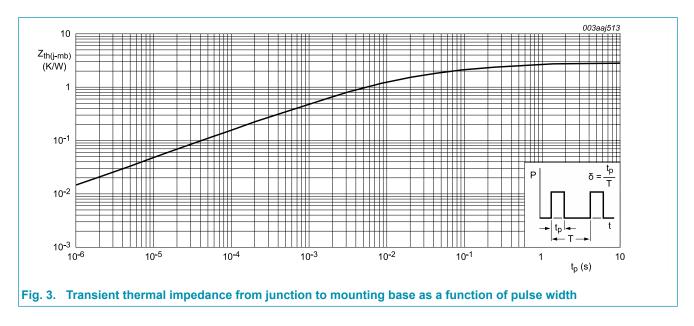


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

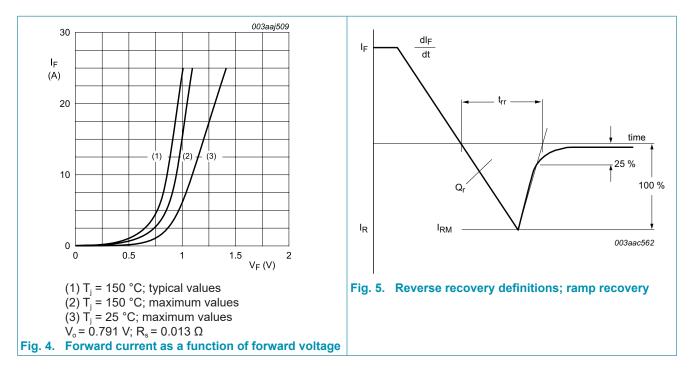
9. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|---------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | <u>Fig. 3</u> | - | - | 2.7 | K/W |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |

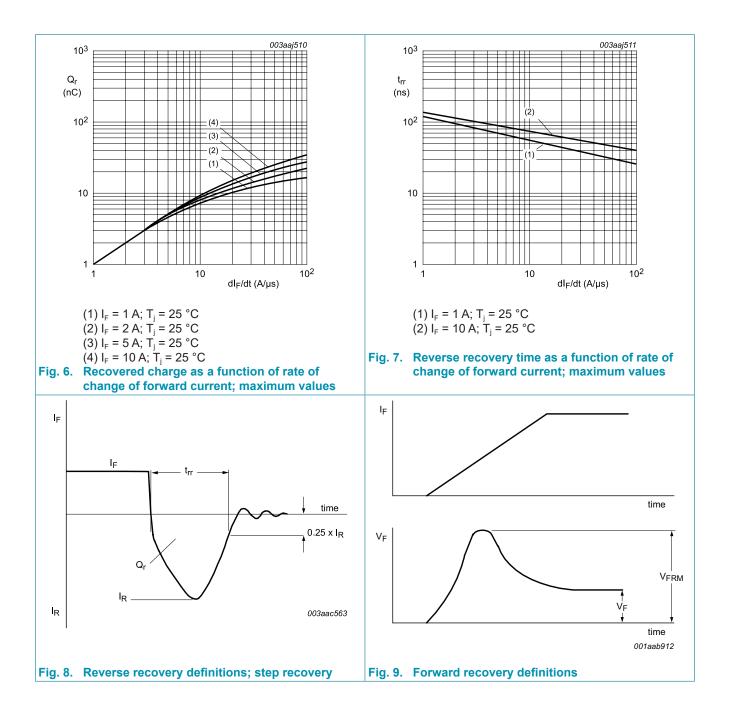


10. Characteristics

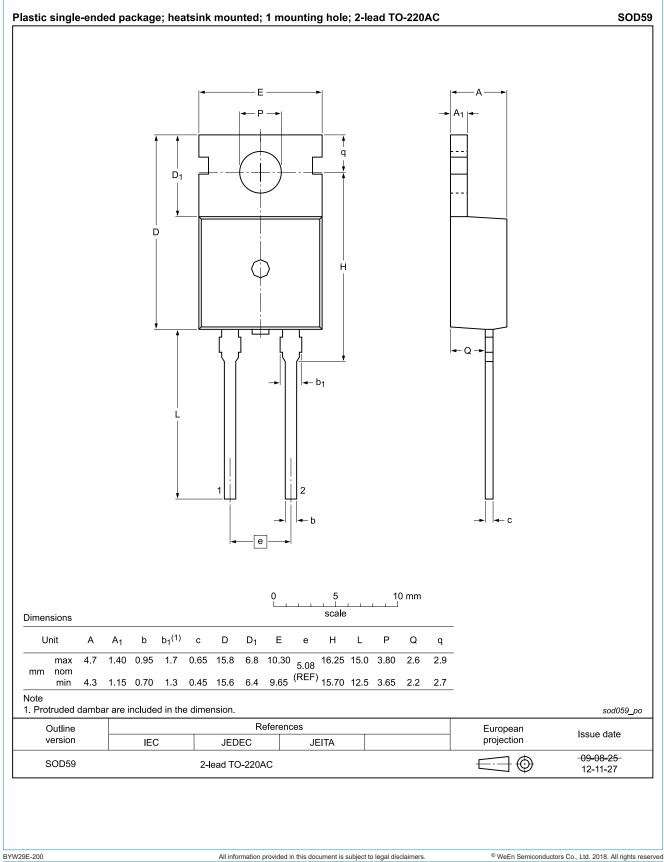
| Symbol | Parameter | Conditions | M | lin | Тур | Max | Unit |
|------------------|--------------------------|--|---|-----|------|-------|------|
| Static cha | racteristics | | | , i | | | |
| V _F | forward voltage | I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u> | - | | 0.92 | 1.05 | V |
| | | I _F = 20 A; T _j = 25 °C; <u>Fig. 4</u> | - | | 1.1 | 1.3 | V |
| | | I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u> | - | | 0.8 | 0.895 | V |
| I _R | reverse current | V _R = 200 V; T _j = 25 °C | - | | 2 | 10 | μA |
| | | V _R = 200 V; T _j = 100 °C | - | | 0.2 | 0.6 | mA |
| Dynamic | characteristics | | | | | | , |
| Q _r | recovered charge | $I_{F} = 2 \text{ A}; V_{R} = 30 \text{ V}; \text{ d}_{F}/\text{d}t = 20 \text{ A}/\mu\text{s}; T_{j} = 25 \text{ °C}; Fig. 5; Fig. 6$ | - | | 4 | 11 | nC |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery; Fig. 5; Fig. 7}$ | - | | 20 | 25 | ns |
| | | $I_{F} = 0.5 \text{ A}; I_{R} = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_{j} = 25 \text{ °C}; \text{ step recovery; Fig. 8}$ | - | | 15 | 20 | ns |
| V _{FRM} | forward recovery voltage | I _F = 1 A; dI _F /dt = 10 A/μs; T _j = 25 °C; <u>Fig. 9</u> | - | | 1 | - | V |



BYW29E-200 Ultrafast power diode



11. Package outline



12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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